

## Silicon NPN Power Transistors

## 2SD898

### DESCRIPTION

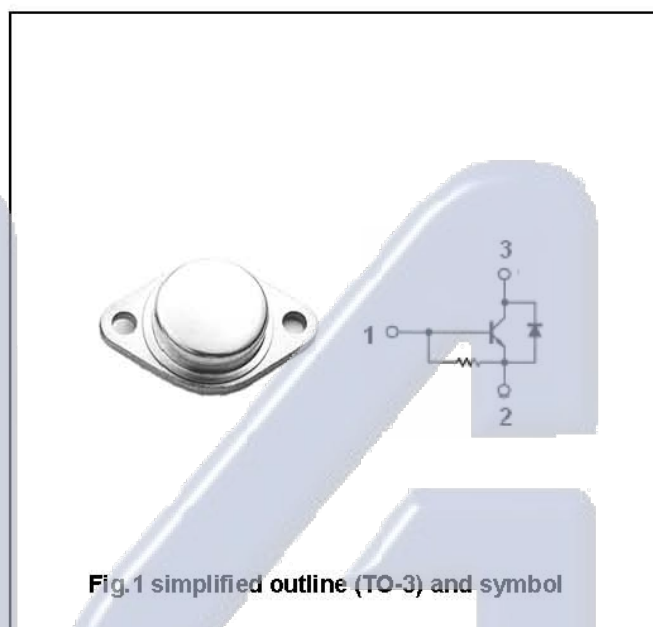
- With TO-3 package
- Built-in damper diode
- High voltage ,high power dissipation
- Wide area of safe operation

### APPLICATIONS

- For TV horizontal deflection output applications

### PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



### Absolute maximum ratings(Ta=°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	1500	V
$V_{CEO}$	Collector-emitter voltage	Open base	1500	V
$V_{EBO}$	Emitter-base voltage	Open collector	6	V
$I_C$	Collector current		3	A
$I_{CM}$	Collector current-peak		3.5	A
$P_T$	Total power dissipation	$T_C=25^\circ\text{C}$	50	W
$T_j$	Junction temperature		150	°C
$T_{stg}$	Storage temperature		-55~150	°C

## Product Specification

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =200mA; I <sub>C</sub> =0;	6			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2.5A; I <sub>B</sub> =0.8 A			5.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =2.5A; I <sub>B</sub> =0.8 A			1.5	V
I <sub>CES</sub>	Collector cut-off current	V <sub>CE</sub> =1500V; R <sub>BE</sub> =0			0.5	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =6V; I <sub>C</sub> =0	50		200	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.5A; V <sub>CE</sub> =5V	10		40	
V <sub>F</sub>	Diode forward voltage	I <sub>F</sub> =3A			2.2	V

*Electrónica S.A. de C.V.*

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PACKAGE OUTLINE

